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Art Unit 2823

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Please amend the claims as follows:

Claim 1. (Amended)

1. A method for forming a junction in a semiconductor device with symmetrical halo implants, comprising the steps of:

forming a photoresist film pattern on a semiconductor substrate excluding a first region;

forming symmetrical first and second implants by performing a first halo implant process and a second halo implant process on the first region of the semiconductor substrate by using a tilt angle of about 45° and twist angles of 0° and 180° corresponding to the first halo implant and second halo implant, respectively; and

performing a third halo implant process on the first region of the semiconductor substrate by using a tilt angle of about 0°.

Claim 4. (Amended)

The method according to claim 1, wherein the third halo implant process is performed only once at a tilt angle of about 0°.

Claim 5. (Amended)

The method according to claim 1, wherein the third halo implant process is performed with an energy of 16KeV and a dose of 4×10^{12} .

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Claim 8. (Amended)

A method for forming a junction with symmetrical halo implants in a semiconductor device, comprising the steps of:

providing a semiconductor substrate divided into a first conductive type MOS region and a second conductive type MOS region;

forming a photoresist film pattern on the second conductive type MOS region;

forming symmetrical first and second halo implants by performing first and second halo implant processes on the first conductive type MOS region at about a 45° tilt angle and at twist angles of about 0° and 180°, respectively;

and

performing a third halo implant process on the first conductive type MOS region, by using a tilt angle of about 0°.

Please add the following new claims:

--14. The method of claim 1, wherein
the first and second halo implants are homogenously doped.

15. The method of claim 8, wherein
the first and second halo implants are homogenously doped.--